TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

## TLP627,TLP627-2,TLP627-4

# PROGRAMMABLE CONTROLLERS DC-OUTPUT MODULE TELECOMMUNICATION

The TOSHIBA TLP627,-2 and -4 consists of a gallium arsenide infrared emitting diode optically coupled to a darlington connected phototransistor which has an integral base-emitter resistor to optimize switching speed and elevated temperature characteristics.

The TLP627-2 offers two isolated channels in a eight lead plastic DIP, while the TLP627-4 provide four isolated channels per package.

Collector-Emitter Voltage : 300V(Min)
 Current Transfer Ratio : 1000%(Min)
 Isolation Voltage : 5000Vrms(Min)

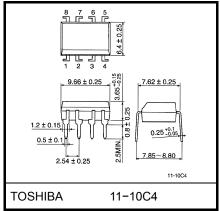
UL Recognized : UL1577, File No. E67349

	MADE IN JA	PAN	MADE IN THAILAND			
UL Recognized	E67349	*1	E152349	*1		
BSI Approved	7426, 7427	*2	7426, 7427	*2		

<sup>\*1</sup> UL1577

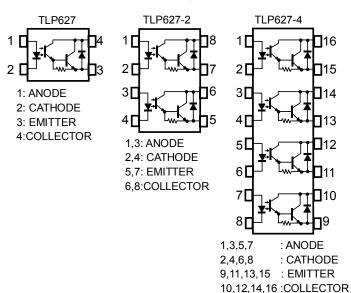
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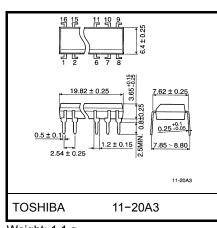
Weight: 0.26 g



Weight: 0.54 g

#### PIN CONFIGURATION (TOP VIEW)





Weight: 1.1 g

<sup>\*2</sup> BS EN60065: 2002, BS EN60950-1: 2002



#### Absolute Maximum Ratings (Ta=25°C)

	CUADACTERICTIC	0)44501	RATING		UNIT	
	CHARACTERISTIC	SYMBOL	TLP627	TLP627-2 TLP627-4	ONT	
	Forward Current	I <sub>F</sub>	60	50	mA	
	Forward Current Derating	ΔI <sub>F</sub> /°C	-0.7(Ta≥39°C)	-0.5(Ta≥25°C)	mA /°C	
	Pulse Forward Current	I <sub>FP</sub>	1(100µs pu	lse,100pps)	Α	
LED	Power Dissipation (1 Circuit)	P <sub>D</sub>	100	70	mW	
	Power Dissipation Derating (Ta≥25°C,1 Circuit)	Δ P <sub>D</sub> /°C	-1.0	-0.7	mW /°C	
	Reverse Voltage	$V_R$	,	5	V	
	Junction Temperature	Tj	1:	25	°C	
	Collector-Emitter Voltage	V <sub>CEO</sub>	30	00	V	
~	Emitter -Collector Voltage	V <sub>ECO</sub>	0	.3	V	
ETECTOR	Collector Current	Ic	1:	mA		
DETE	Collector Power Dissipation (1 Circuit)	Pc	150(*300)	100	mW	
	Collector Power Dissipation Derating (Ta≥25°C,1 Circuit)	ΔP <sub>c</sub> /°C	-1.5(*-3.5)	-1.0	mW /°C	
	Junction Temperature	Tj	1:	25	°C	
Оре	rating Temperature Range	T <sub>opr</sub>	-55 <sup>-</sup>	~100	°C	
Stor	rage Temperature Range	T <sub>stg</sub>	-55~125		°C	
Lea	d Soldering Temperature (10s)	T <sub>sold</sub> 260(10sec)		°C		
Tota	al Package Power Dissipation	P <sub>T</sub>	250(*320)	150	mW	
Tota	al Package Power Dissipation Derating (Ta≥25°C,1 Circuit)	Δ P <sub>T</sub> /°C	-2.5(*-3.2)	-1.5	mW /°C	
Isola	ation Voltage (AC,1min. , R.H.≤60%) (Note1)	BVs	50	000	Vrms	

\*IF=20mA Max

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note1)Device considered a two terminal device : LED side pins Shorted together and DETECTOR side pins shorted together.

#### **Recommended Operating Conditions**

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V <sub>CC</sub>	_	_	200	٧
Forward Current	I <sub>F</sub>	_	16	25	mA
Collector Current	Ic	_	_	120	mA
Operating Temperature	$T_{opr}$	-25	1	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.



## Individual Electrical Characteristics (Ta=25°C)

	CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
	Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 10 mA		1.15	1.3	V
LED	Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 5 V		_	10	μA
	Capacitance	Ст	V = 0 , f=1MHz	_	30	_	pF
	Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	IC = 0.1mA	300	_	_	V
DETECTOR	Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	IE = 0.1mA	0.3	_	_	V
TEC	Collector Dark Current		V <sub>CE</sub> = 200V	_	10	200	nA
DE	$\square$ Collector Dark Current $  I_{CEO}  $ $  V_{CE} = 200V$ , Ta = 85°C		V <sub>CE</sub> = 200V , Ta = 85°C	_	_	20	μA
	Capacitance Collector to Emitter	C <sub>CE</sub>	V=0 , f=1MHz	- 1	10	_	pF

## Coupled Electrical Characteristics (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I <sub>C</sub> /I <sub>F</sub>	I <sub>F</sub> =1mA , V <sub>CE</sub> =1V	1000	4000	_	%
Saturated CTR	I <sub>C</sub> /I <sub>F</sub> (sat)	I <sub>F</sub> =10mA , V <sub>CE</sub> =1V	500	_	_	%
Collector-Emitter	V (eat)	I <sub>C</sub> =10mA , I <sub>F</sub> =1mA	_	_	1.0	V
Saturation Voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> =100mA , I <sub>F</sub> =10mA	0.3	_	1.2	V

### Isolation Electrical Characteristics (Ta=25°C)

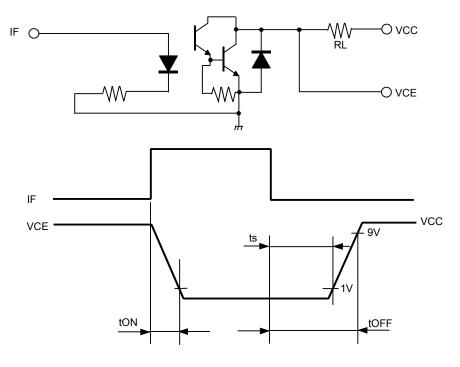
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance Input to Output	Cs	V <sub>S</sub> =0 , f=1MHz	_	0.8	_	pF
Isolation Resistance	Rs	V <sub>S</sub> =500V , R.H.≤60%	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
Isolation Voltage		AC, 1minute 5000 —  BVs AC, 1second, in oil — 1000	_	_	Vrms	
	BVs		10000	_	VIIIIS	
		DC, 1 minute, in oil	_	10000	_	Vdc

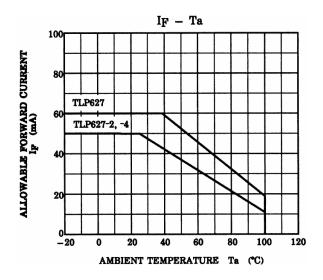


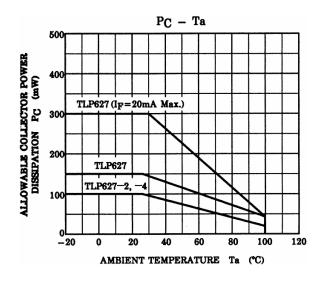
## **Switching Characteristics (Ta=25°C)**

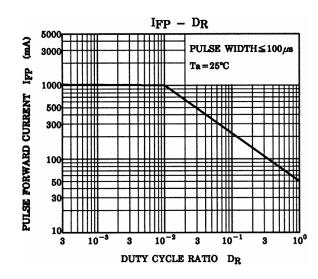
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	tr		_	40	_	
Fall Time	tf	$V_{cc}$ =10V $I_{c}$ =10mA	_	15	_	
Turn-on Time	ton	$R_L$ =100 $\Omega$	_	50	_	
Turn-off Time	toff		_	15	_	μs
Turn-on Time	tON	R <sub>L</sub> =180Ω (Fig.1) V <sub>CC</sub> =10V , I <sub>F</sub> =16mA	_	5	_	
Strage Time	ts		_	40	_	
Turn-off Time	tOFF		_	80	_	

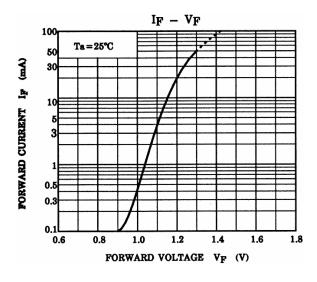
### Fig.1 SWITCHING TIME TEST CIRCUIT

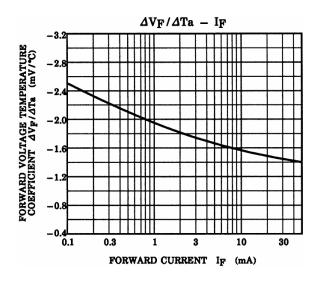


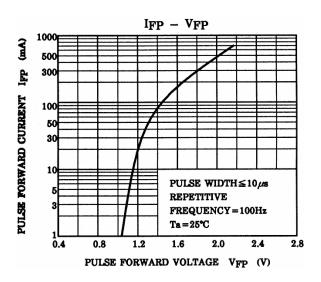


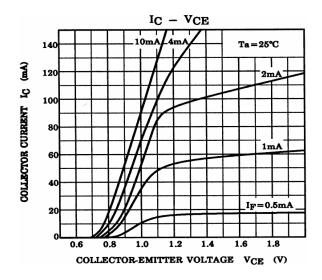


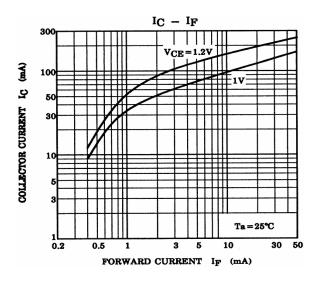


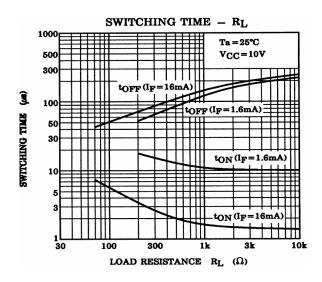


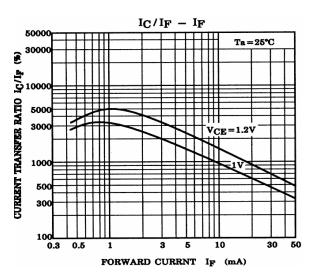


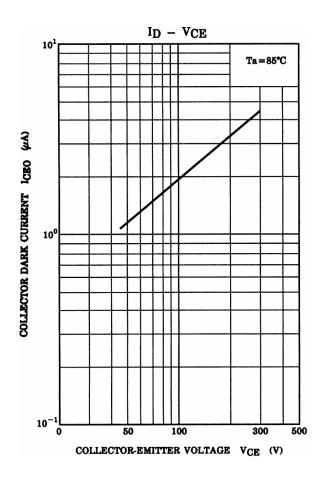


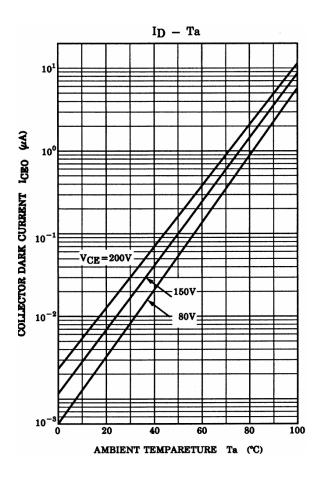


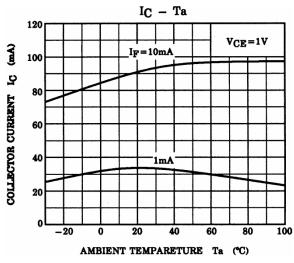


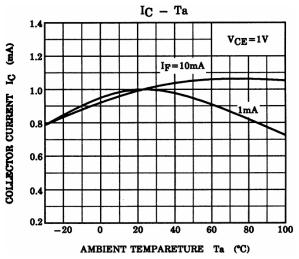












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